

SCT2450KE

N-channel SiC power MOSFET

V_{DSS}	1200V
R _{DS(on)} (Typ.)	450mΩ
I _D	10A
P_{D}	85W

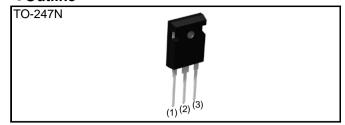
Features

- 1) Low on-resistance
- 2) Fast switching speed
- 3) Fast reverse recovery
- 4) Easy to parallel
- 5) Simple to drive
- 6) Pb-free lead plating; RoHS compliant

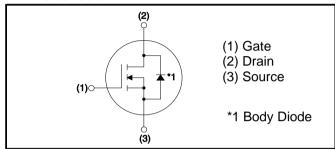
Application

- Solar inverters
- DC/DC converters
- · Induction heating
- Motor drives

Outline



•Inner circuit



Packaging specifications

Packa	age TO-247N	
	Packing	Tube
Reel size (mm)	-	
Typo	Tape width (mm)	-
Туре	Basic ordering unit (pcs)	30
	Packing code	C11
	Marking	SCT2450KE

● Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Value	Unit	
Drain - Source voltage		V_{DSS}	1200	V
Continuous drain current	T _c = 25°C	I _D *1	10	А
Continuous drain current	T _c = 100°C	I _D *1	7	А
Pulsed drain current		I _{D,pulse} *2	25	А
Gate - Source voltage (DC)		V_{GSS}	−6 to 22	V
Gate - Source surge voltage (T _{surge} < 300nsec)		V _{GSS-surge} *3	–10 to 26	V
Power dissipation (T _c = 25°C)		P _D	85	W
Junction temperature		T _j	175	°C
Range of storage temperature		T _{stg}	-55 to +175	°C

●Electrical characteristics (T_a = 25°C)

Parameter	Cumbal	Conditions	Values			Unit	
- Farameter	Symbol	Conditions	Min.	Тур.	Max.	Offic	
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V$, $I_D = 1mA$	1200	ı	1	V	
Zero gate voltage drain current	I _{DSS}	$V_{DS} = 1200V, V_{GS} = 0V$ $T_{j} = 25^{\circ}C$ $T_{j} = 150^{\circ}C$	-	1 2	10	μΑ	
Gate - Source leakage current	I _{GSS+}	$V_{GS} = +22V, V_{DS} = 0V$	1	1	100	nA	
Gate - Source leakage current	I _{GSS} _	$V_{GS} = -6V, V_{DS} = 0V$	-	-	-100	nA	
Gate threshold voltage	$V_{GS (th)}$	$V_{DS} = V_{GS}$, $I_D = 0.9 \text{mA}$	1.6	2.8	4.0	V	

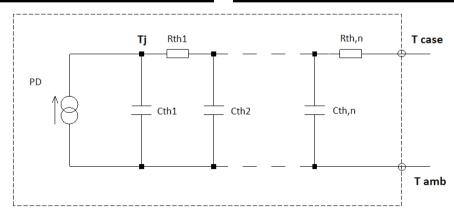
●Thermal resistance

Parameter	Symbol	Values			Unit
Parameter	Symbol	Min.	Тур.	Max.	Offic
Thermal resistance, junction - case	R _{thJC}	-	1.36	1.77	°C/W
Thermal resistance, junction - ambient	R _{thJA}	-	-	50	°C/W
Soldering temperature, wavesoldering for 10s	T_{sold}	-	-	265	°C

● Typical Transient Thermal Characteristics

Symbol	Value	Unit
R _{th1}	2.30E-01	
R _{th2}	6.87E-01	K/W
R _{th3}	4.41E-01	

Symbol	Value	Unit
C _{th1}	2.19E-04	
C _{th2}	1.29E-03	Ws/K
C _{th3}	1.31E-02	



●Electrical characteristics (T_a = 25°C)

Danamatan	Symbol	Conditions	Values			Unit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
		$V_{GS} = 18V, I_D = 3A$				
Static drain - source on - state resistance	R _{DS(on)} *4	T _j = 25°C	-	450	585	mΩ
		T _j = 125°C	-	610	-	
Gate input resistance	R_{G}	f = 1MHz, open drain	-	25	-	Ω
Transconductance	g fs *4	$V_{DS} = 10V, I_D = 3A$	-	1.0	-	S
Input capacitance	C _{iss}	$V_{GS} = 0V$	-	463	-	
Output capacitance	C _{oss}	V _{DS} = 800V	-	21	-	pF
Reverse transfer capacitance	C _{rss}	f = 1MHz	-	4	-	
Effective output capacitance, energy related	C _{o(er)}	$V_{GS} = 0V$ $V_{DS} = 0V$ to 500V	-	31	-	pF
Turn - on delay time	t _{d(on)} *4	$V_{DD} = 400V, V_{GS} = 18V$	-	19	-	
Rise time	t _r *4	$I_D = 3A$	-	17	-	
Turn - off delay time	t _{d(off)} *4	R _L = 133Ω	-	38	-	ns
Fall time	t _f *4	$R_G = 0\Omega$	-	34	-	
Turn - on switching loss	E _{on} *4	$V_{DD} = 600V, I_{D} = 3A$ $V_{GS} = 18V/0V$	-	47	-	1
Turn - off switching loss	E _{off} *4	R _G = 0Ω, L=500μH *E _{on} includes diode reverse recovery	-	17	-	μJ

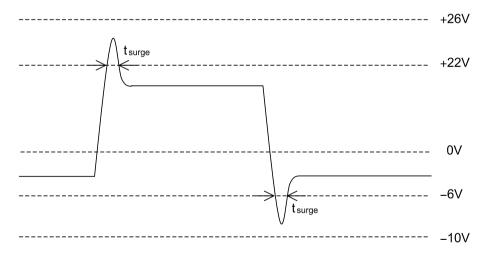
•Gate Charge characteristics $(T_a = 25^{\circ}C)$

Parameter	Symbol	Conditions	Values			Unit
			Min.	Тур.	Max.	Offic
Total gate charge	Q_g^{*4}	V _{DD} = 400V	-	27	-	
Gate - Source charge	Q _{gs} *4	$I_D = 3A$	-	7	-	nC
Gate - Drain charge	Q _{gd} *4	V _{GS} = 18V	-	9	-	
Gate plateau voltage	V _(plateau)	$V_{DD} = 400V, I_{D} = 3A$	-	10.5	-	V

•Body diode electrical characteristics (Source-Drain) ($T_a = 25$ °C)

Doromotor	Coursels al	Open ditions	Values			l linit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Inverse diode continuous, forward current	l _S *1	-T _c = 25°C	-	-	10	А
Inverse diode direct current, pulsed	I _{SM} *2		-	-	25	А
Forward voltage	V _{SD} *45	$V_{GS} = 0V$, $I_S = 3A$	-	4.3	-	V
Reverse recovery time	t _{rr} *4		-	19	-	ns
Reverse recovery charge	Q _{rr} *4	I _F = 3A, V _R = 400V di/dt = 110A/μs		13	-	nC
Peak reverse recovery current	I _{rrm} *4		-	1.4	-	Α

^{*3} Example of acceptable V_{GS} waveform



*4 Pulsed

^{*1} Limited only by maximum temperature allowed.

^{*2} PW \leq 10 μ s, Duty cycle \leq 1%

Fig.1 Power Dissipation Derating Curve

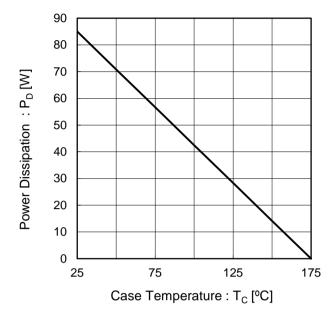


Fig.2 Maximum Safe Operating Area

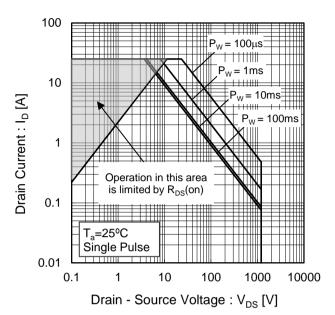


Fig.3 Typical Transient Thermal Resistance vs. Pulse Width

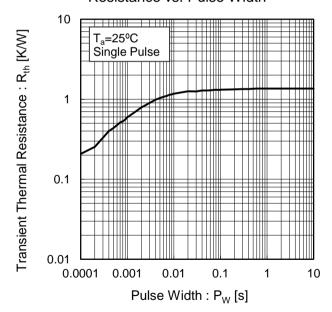
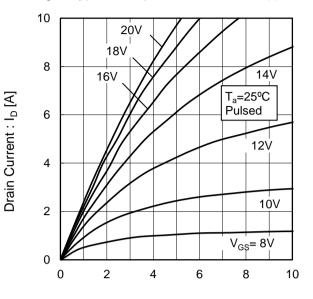
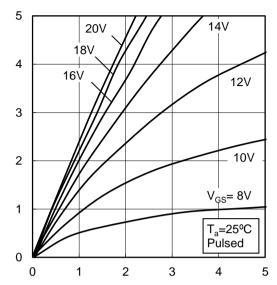


Fig.4 Typical Output Characteristics(I)



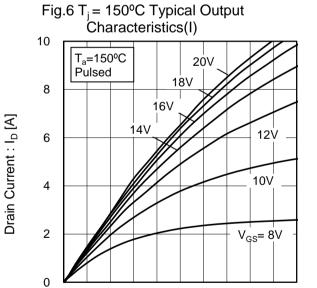
Drain - Source Voltage : V_{DS} [V]

Fig.5 Typical Output Characteristics(II)



Drain Current : I_D [A]

Drain - Source Voltage : V_{DS} [V]

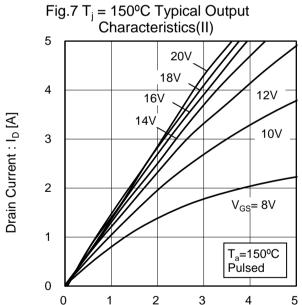


Drain - Source Voltage : V_{DS} [V]

6

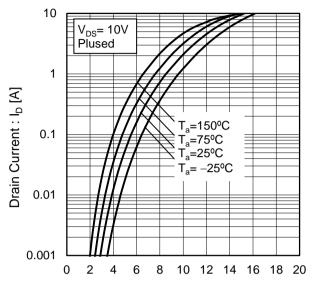
8

10



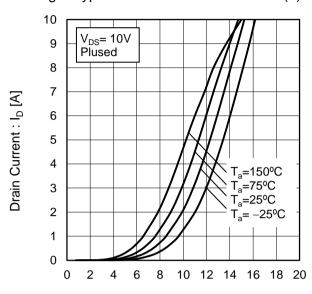
Drain - Source Voltage: V_{DS} [V]

Fig.8 Typical Transfer Characteristics (I)

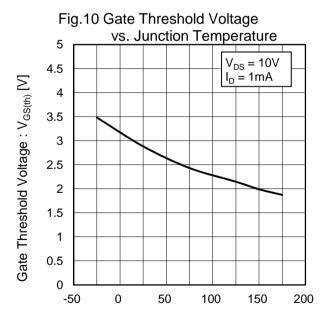


Gate - Source Voltage : $V_{GS}[V]$

Fig.9 Typical Transfer Characteristics (II)

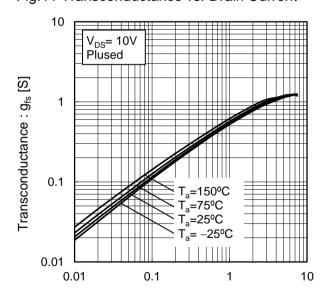


Gate - Source Voltage : V_{GS} [V]

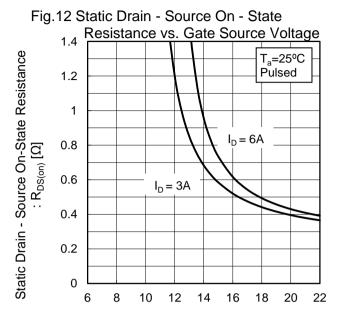


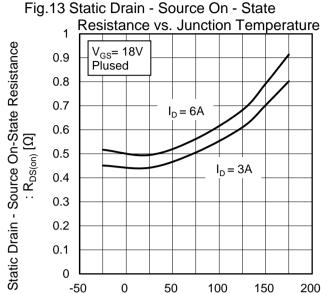
Junction Temperature : T_i [°C]

Fig.11 Transconductance vs. Drain Current



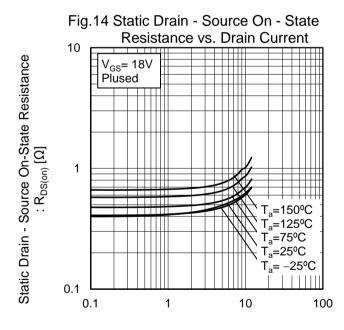
Drain Current : I_D [A]



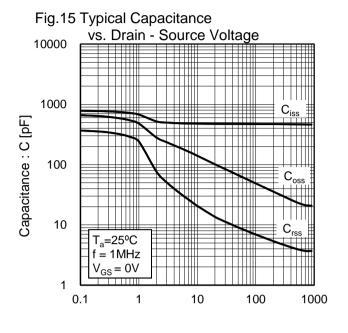


Gate - Source Voltage : V_{GS} [V]

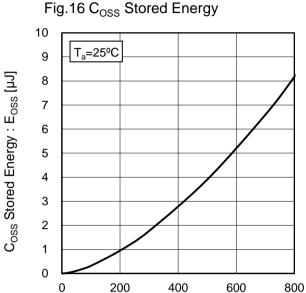
Junction Temperature : T_i [°C]



Drain Current : I_D [A]



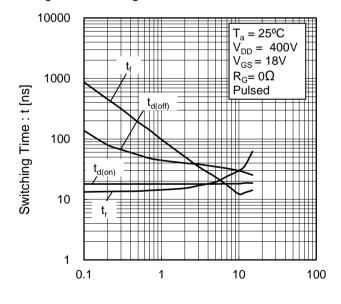
Drain - Source Voltage : V_{DS} [V]



Drain - Source Voltage : V_{DS} [V]

Fig.18 Dynamic Input Characteristics

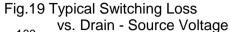
Fig.17 Switching Characteristics

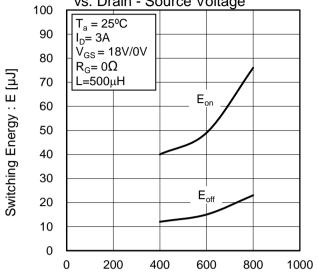


Drain Current : I_D [A]

Gate - Source Voltage : V_{GS} [V]

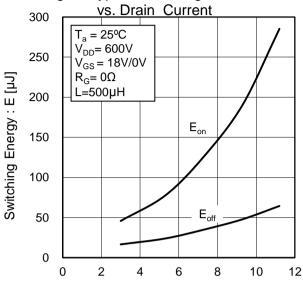
Total Gate Charge : Q_q [nC]





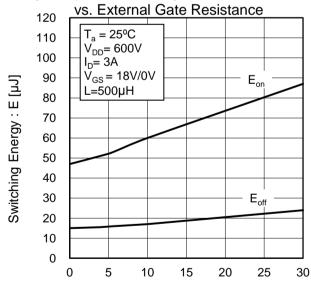
Drain - Source Voltage: V_{DS} [V]

Fig.20 Typical Switching Loss

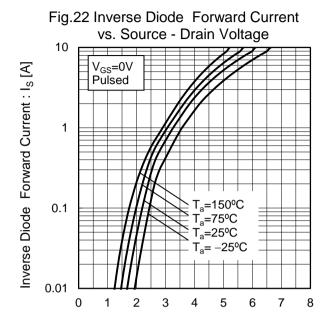


Drain Current : I_D [A]

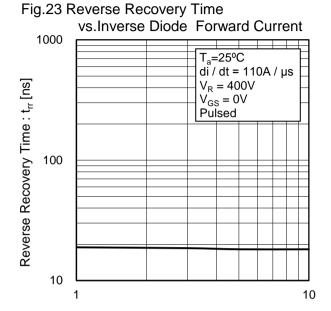
Fig.21 Typical Switching Loss



External Gate Resistance : $R_G [\Omega]$



Source - Drain Voltage : V_{SD} [V]



Inverse Diode Forward Current : I_S [A]

Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

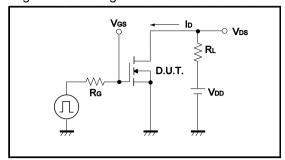


Fig.2-1 Gate Charge Measurement Circuit

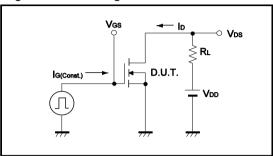


Fig.3-1 Switching Energy Measurement Circuit

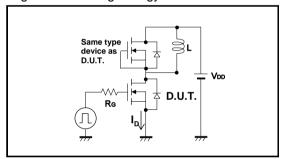


Fig.4-1 Reverse Recovery Time Measurement Circuit Fig.4-2 Reverse Recovery Waveform

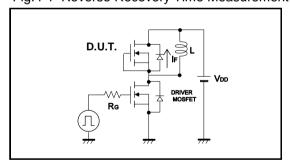


Fig.1-2 Switching Waveforms

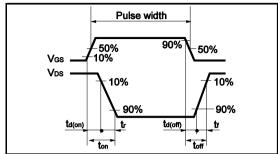


Fig.2-2 Gate Charge Waveform

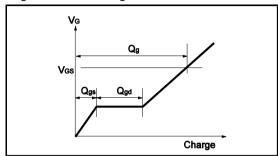
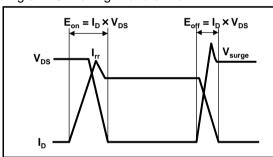
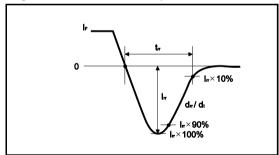


Fig.3-2 Switching Waveforms





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